2SD0662, 2SD0662B (2SD662, 2SD662B)

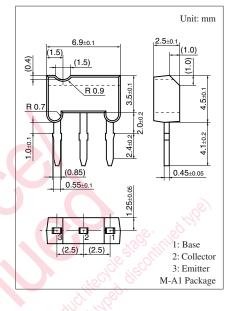
Silicon NPN epitaxial planar type

For high breakdown voltage general amplification

Features

- High collector-emitter voltage (Base open) V_{CEO}
- \bullet High transition frequency f_{T}
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

Symbol Parameter Rating Unit V 250 2SD0662 V_{CBO} Collector-base voltage (Emitter open) 2SD0662B 400 2SD0662 V_{CEO} 200 V Collector-emitter voltage (Base open) 2SD0662B 400 Emitter-base voltage (Collector open) 5 V V_{EBO} 70 Collector current I_C mA Collector power dissipation P_{C} 600 mW Junction temperature Ti 150 °C T_{stg} Storage temperature -55 to +150 °C



Absolute Maximum Ratings $T_a = 25^{\circ}C$

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SD0662	V _{CEO}	$I_{\rm C} = 100 \ \mu {\rm A}, I_{\rm B} = 0$	200			V
(Base open)	2SD0662B		and allo	400			
Emitter-base voltage (Collector open)		V _{EBO}	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	5			V
Collector-emitter cutoff current (Base open)		I _{CEO}	$V_{CE} = 100 \text{ V}, \text{ I}_{B} = 0$			2	μΑ
Forward current transfer ratio		h _{FE} *	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	30		220	
Collector-emitter saturation voltage		V _{CE(sat)}	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5 \text{ mA}$			1.2	V
Transition frequency		fT	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$	50			MHz
Collector output capacitance (Common base, input open circuited)		Cob	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$			10	pF

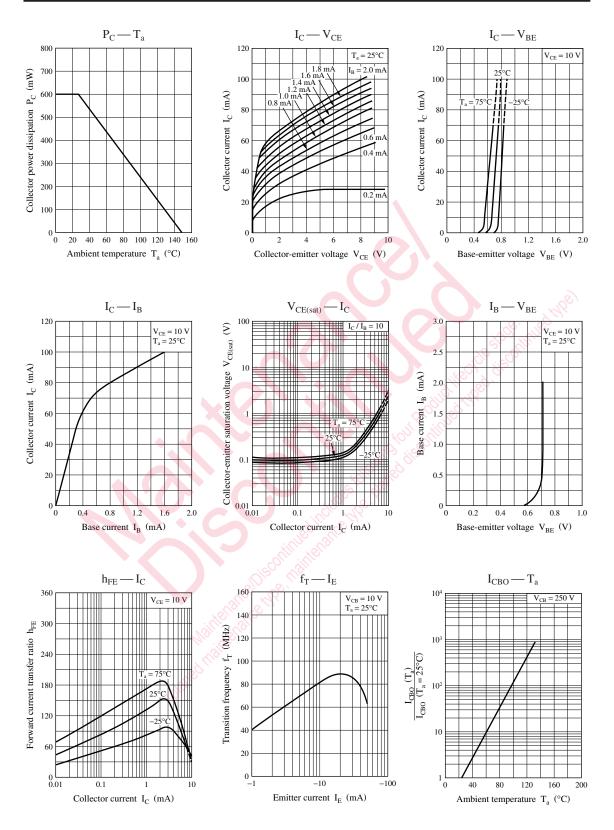
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Р	Q	R	
$h_{\rm FE}$	30 to 100	60 to 150	100 to 220	

Note) The part numbers in the parenthesis show conventional part number.

Panasonic



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